

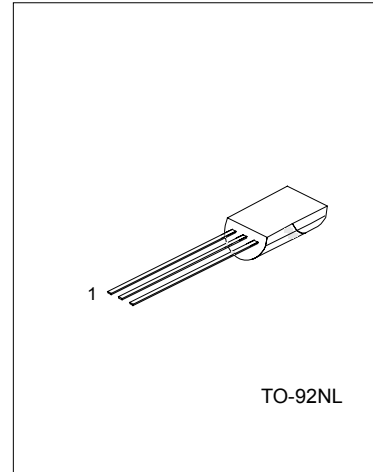
UTC 2SA928A

PNP EPITAXIAL SILICON TRANSISTOR

AUDIO POWER AMPLIFIER

FEATURES

- *Collector Dissipation $P_c=1$ W
- *3 W Output Application
- *Complement of 2SC2328A



1: EMITTER 2: COLLECTOR 3: BASE

ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	RATING	UNIT
Collector-base voltage	V _{CB0}	-30	V
Collector-emitter voltage	V _{CEO}	-30	V
Emitter-base voltage	V _{EB0}	-5	V
Collector dissipation	P _c	1	W
Collector current	I _c	-2	A
Junction Temperature	T _j	150	°C
Storage Temperature	T _{STG}	-55 ~ +150	°C

ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	BV _{CB0}	I _c =-100μA, I _E =0	-30			V
Collector-emitter breakdown voltage	BV _{CEO}	I _c =-10mA, I _B =0	-30			V
Emitter-base breakdown voltage	BV _{EB0}	I _E =-1mA, I _c =0	-5			V
Collector cut-off current	I _{CB0}	V _{CB} =-30V, I _E =0			-100	nA
Emitter cut-off current	I _{EB0}	V _{BE} =-5V, I _c =0			-100	nA
DC current gain(note)	h _{FE}	V _{CE} =-2V, I _c =-500mA	100		320	
Base-emitter on voltage	V _{BE(on)}	V _{CE} =-2V, I _c =-500mA			-1	V
Collector-emitter saturation voltage	V _{CE(sat)}	I _c =-1.5A, I _B =-0.03A			-2	V
Output capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f=1MHz		48		pF
Current gain bandwidth product	f _t	V _{CE} =-2V, I _c =-500mA		120		MHz

CLASSIFICATION OF hFE

RANK	O	Y
RANGE	100-200	160-320

TYPICAL CHARACTERISTIC CURVES

